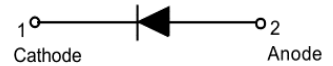
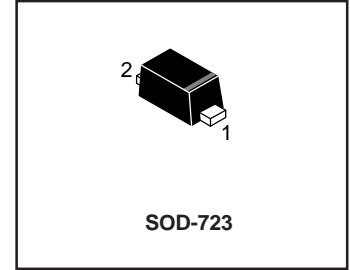


# RB520G-30

## S-RB520G-30

Schottky barrier diode



### 1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Ultra Small mold type.
- Low IR
- High reliability.

### 2. Construction

- Silicon epitaxial planar

### 3. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
RB520G-30	E	4000/Tape&Reel

### 4. MAXIMUM RATINGS(Ta = 25°C)

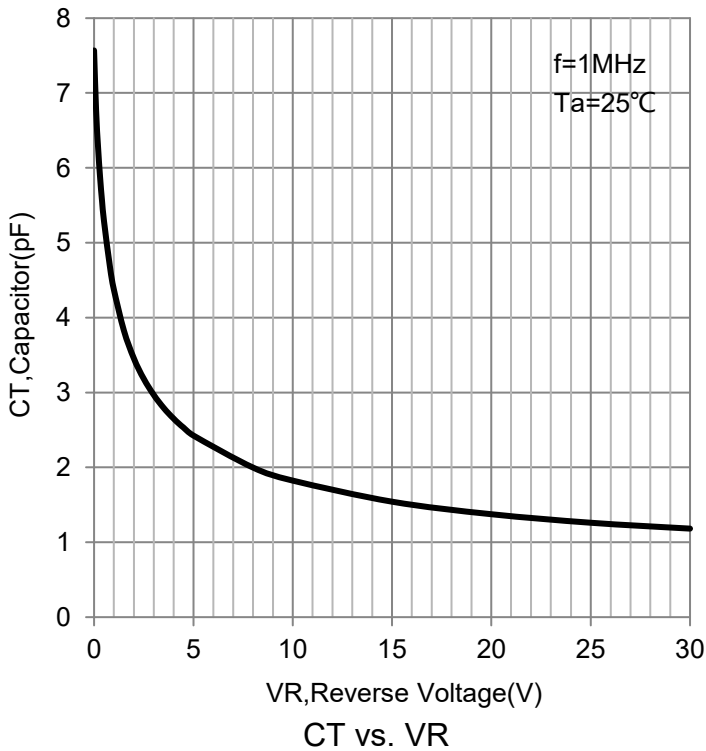
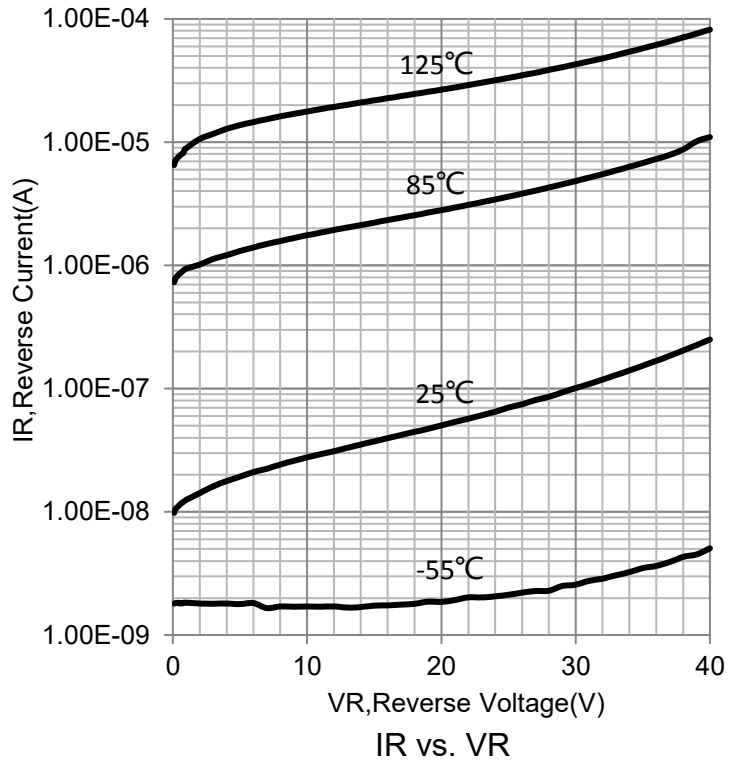
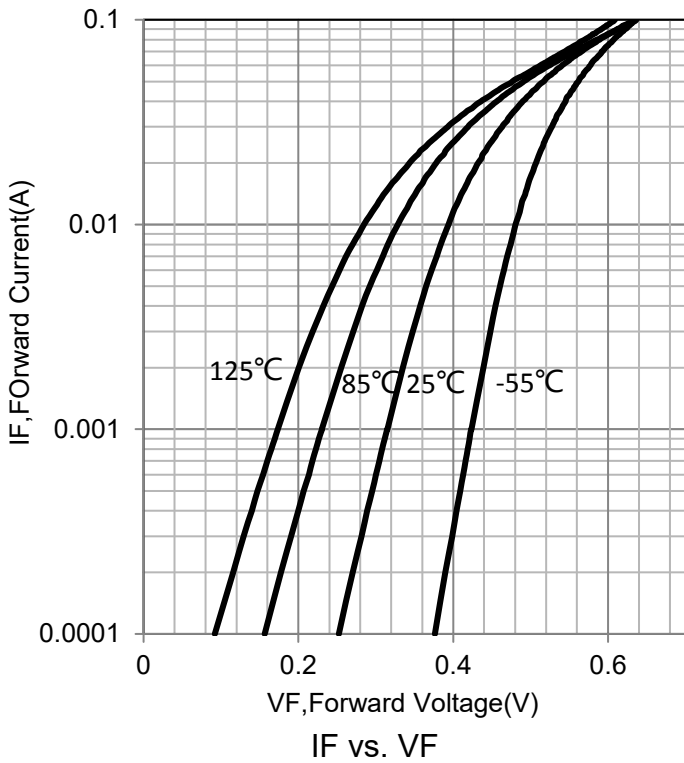
Parameter	Symbol	Limits	Unit
Reverse voltage(DC)	VR	30	V
Average rectified forward current	IO	100	mA
Forward current surge peak (60Hz · 1cyc)	IFSM	500	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-40~+125	°C

### 5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

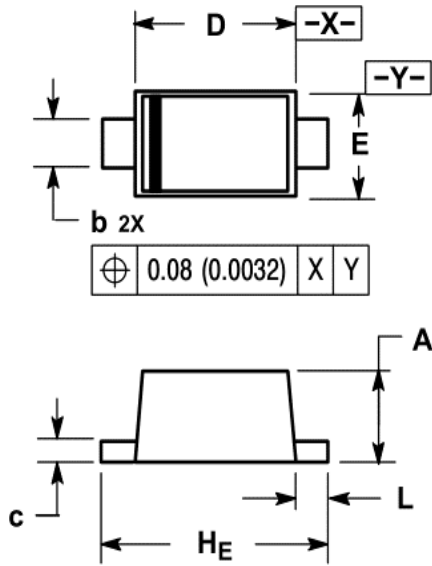
CHARACTERISTICS	Symbol	Min	Typ	Max	Unit
Forward voltage (IF=10mA)	VF	-	-	0.45	V
Reverse current (VR=10V)	IR	-	-	0.5	μA



6.ELECTRICAL CHARACTERISTICS CURVES



**7.OUTLINE AND DIMENSIONS**



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

Dim	MILLIMETERS			NCES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.49	0.52	0.55	0.019	0.020	0.022
b	0.25	0.28	0.32	0.0098	0.011	0.013
c	0.08	0.12	0.15	0.0032	0.0047	0.0059
D	0.95	1.00	1.05	0.037	0.039	0.041
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	1.35	1.40	1.45	0.053	0.055	0.057
L	0.15	0.2	0.25	0.006	0.0079	0.010

**8.SOLDERING FOOTPRINT**

